



ON Semiconductor®

# FQD4N25

## N-Channel QFET® MOSFET

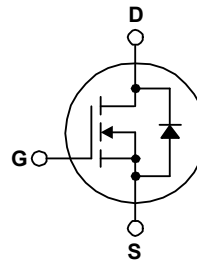
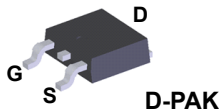
250 V, 3 A, 1.75 Ω

### Description

This N-Channel enhancement mode power MOSFET is produced using ON Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power factor correction (PFC), and electronic lamp ballasts.

### Features

- 3 A, 250 V,  $R_{DS(on)} = 1.75 \Omega$  (Max.) @  $V_{GS} = 10 V$ ,  $I_D = 1.5 A$
- Low Gate Charge (Typ. 4.3 nC)
- Low Crss (Typ. 4.8 pF)
- 100% Avalanche Tested



### Absolute Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted.

Symbol	Parameter	FQD4N25TM-WS	Unit
V <sub>DSS</sub>	Drain-Source Voltage	250	V
I <sub>D</sub>	Drain Current - Continuous (T <sub>C</sub> = 25°C) - Continuous (T <sub>C</sub> = 100°C)	3.0	A
		1.9	A
I <sub>DM</sub>	Drain Current - Pulsed (Note 1)	12	A
V <sub>GSS</sub>	Gate-Source Voltage	± 30	V
E <sub>AS</sub>	Single Pulsed Avalanche Energy (Note 2)	52	mJ
I <sub>AR</sub>	Avalanche Current (Note 1)	3.0	A
E <sub>AR</sub>	Repetitive Avalanche Energy (Note 1)	3.7	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	5.5	V/ns
P <sub>D</sub>	Power Dissipation (T <sub>A</sub> = 25°C) *	2.5	W
	Power Dissipation (T <sub>C</sub> = 25°C)	37	W
	- Derate above 25°C	0.29	W/°C
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range	-55 to +150	°C
T <sub>L</sub>	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds.	300	°C

### Thermal Characteristics

Symbol	Parameter	FQD4N25TM_WS	Unit
R <sub>θJC</sub>	Thermal Resistance, Junction to Case, Max.	3.4	°C/W
R <sub>θJA</sub>	Thermal Resistance, Junction to Ambient (Minimum Pad of 2-oz Copper), Max.	110	
	Thermal Resistance, Junction to Ambient (*1 in <sup>2</sup> Pad of 2-oz Copper), Max.	50	

FQD4N25 — N-Channel QFET® MOSFET

## Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FQD4N25TM-WS	FQD4N25S	DPAK	Tape and Reel	330 mm	16 mm	2500 units

## Electrical Characteristics

$T_C = 25^\circ\text{C}$  unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
<b>Off Characteristics</b>						
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	250	--	--	V
$\Delta BV_{DSS} / \Delta T$	Breakdown Voltage Temperature Coefficient	$I_D = 250\ \mu\text{A}$ , Referenced to $25^\circ\text{C}$	--	0.22	--	$\text{V}/^\circ\text{C}$
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 250\text{ V}, V_{GS} = 0\text{ V}$	--	--	1	$\mu\text{A}$
		$V_{DS} = 200\text{ V}, T_C = 125^\circ\text{C}$	--	--	10	$\mu\text{A}$
$I_{GSSF}$	Gate-Body Leakage Current, Forward	$V_{GS} = 30\text{ V}, V_{DS} = 0\text{ V}$	--	--	100	nA
$I_{GSSR}$	Gate-Body Leakage Current, Reverse	$V_{GS} = -30\text{ V}, V_{DS} = 0\text{ V}$	--	--	-100	nA

## On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	3.0	--	5.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 10\text{ V}, I_D = 1.5\text{ A}$	--	1.38	1.75	$\Omega$
$g_{FS}$	Forward Transconductance	$V_{DS} = 50\text{ V}, I_D = 1.5\text{ A}$	--	2.4	--	S

## Dynamic Characteristics

$C_{iss}$	Input Capacitance	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$	--	155	200	pF
$C_{oss}$	Output Capacitance		--	35	45	pF
$C_{rss}$	Reverse Transfer Capacitance		--	4.8	6.5	pF

## Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 125\text{ V}, I_D = 3.6\text{ A},$ $R_G = 25\ \Omega$	--	6.8	25	ns
$t_r$	Turn-On Rise Time		--	45	100	ns
$t_{d(off)}$	Turn-Off Delay Time	(Note 4)	--	6.4	25	ns
$t_f$	Turn-Off Fall Time		--	22	55	ns
$Q_g$	Total Gate Charge	$V_{DS} = 200\text{ V}, I_D = 3.6\text{ A},$ $V_{GS} = 10\text{ V}$	--	4.3	5.6	nC
$Q_{gs}$	Gate-Source Charge		--	1.3	--	nC
$Q_{gd}$	Gate-Drain Charge		(Note 4)	--	2.1	--

## Drain-Source Diode Characteristics and Maximum Ratings

$I_S$	Maximum Continuous Drain-Source Diode Forward Current	--	--	3.0	A	
$I_{SM}$	Maximum Pulsed Drain-Source Diode Forward Current	--	--	12	A	
$V_{SD}$	Drain-Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = 3.0\text{ A}$	--	--	1.5	V
$t_{rr}$	Reverse Recovery Time	$V_{GS} = 0\text{ V}, I_S = 3.6\text{ A},$ $dI_F / dt = 100\text{ A}/\mu\text{s}$	--	110	--	ns
$Q_{rr}$	Reverse Recovery Charge		--	0.35	--	$\mu\text{C}$

### Notes:

1. Repetitive rating : pulse-width limited by maximum junction temperature.
2.  $L = 9.3\text{ mH}, I_{AS} = 3.0\text{ A}, V_{DD} = 50\text{ V}, R_G = 25\ \Omega$ , starting  $T_J = 25^\circ\text{C}$ .
3.  $I_{SD} \leq 3.6\text{ A}, di/dt \leq 300\text{ A}/\mu\text{s}, V_{DD} \leq BV_{DSS}$ , starting  $T_J = 25^\circ\text{C}$ .
4. Essentially independent of operating temperature.

## Typical Characteristics

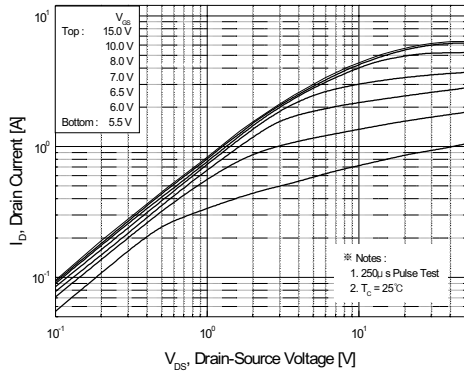


Figure 1. On-Region Characteristics

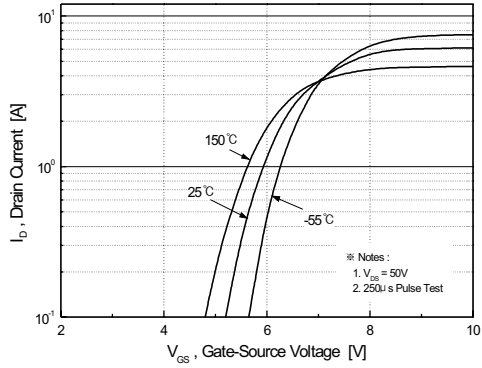


Figure 2. Transfer Characteristics

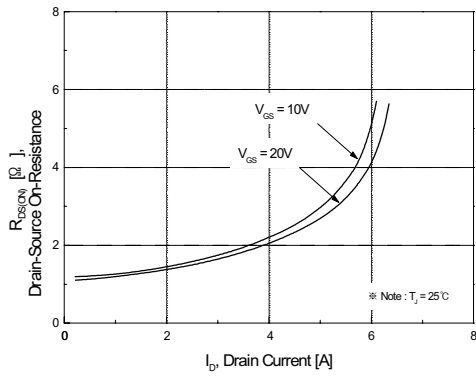


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

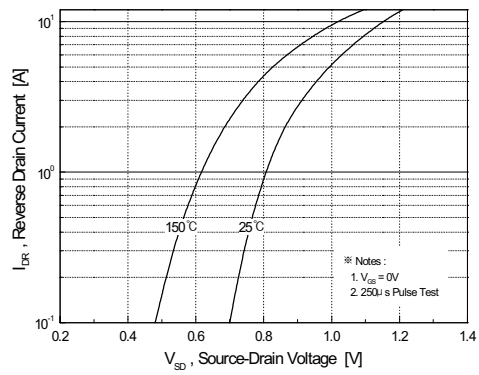


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

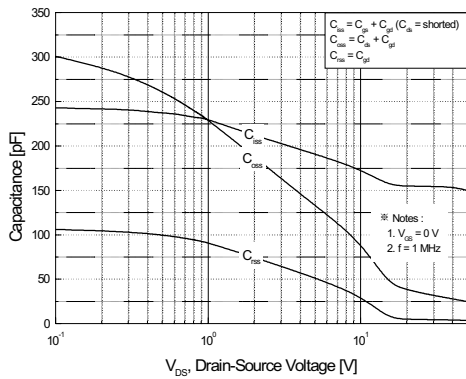


Figure 5. Capacitance Characteristics

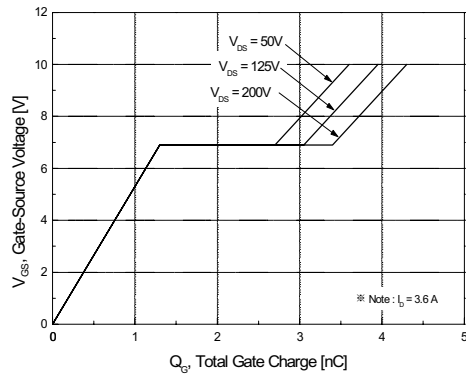
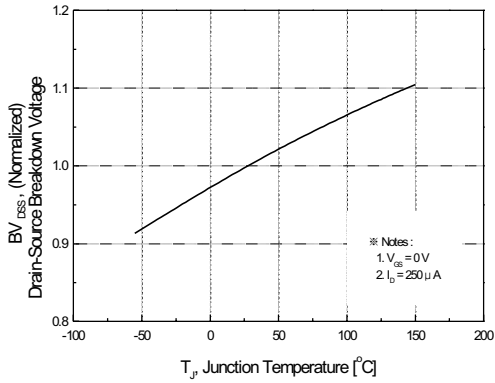
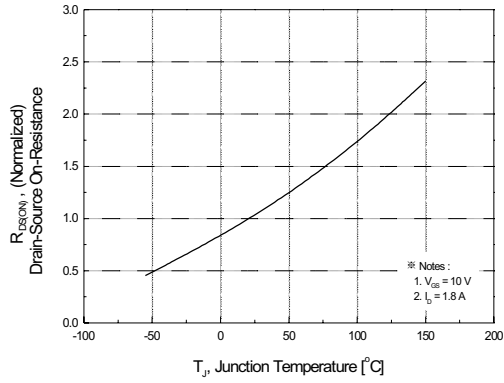


Figure 6. Gate Charge Characteristics

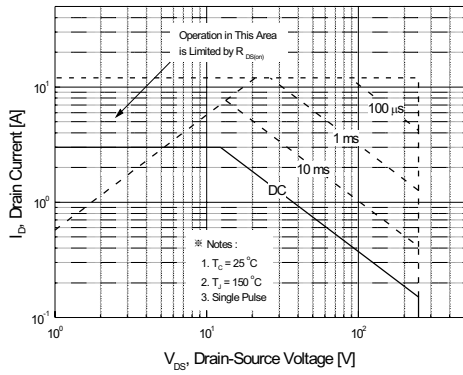
**Typical Characteristics** (Continued)



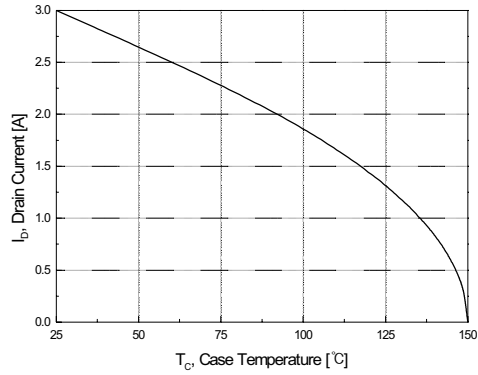
**Figure 7. Breakdown Voltage Variation vs. Temperature**



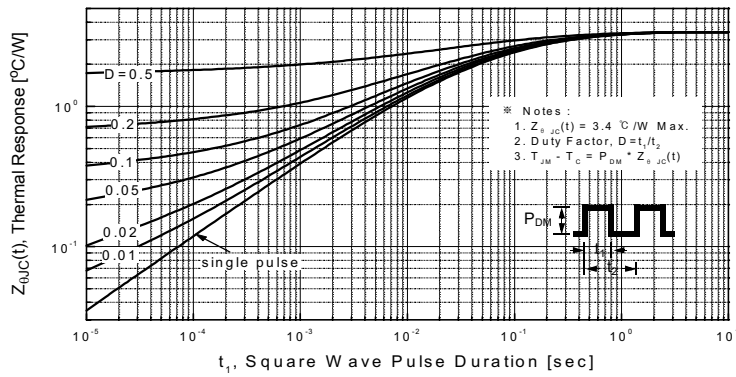
**Figure 8. On-Resistance Variation vs. Temperature**



**Figure 9. Maximum Safe Operating Area**



**Figure 10. Maximum Drain Current vs. Case Temperature**



**Figure 11. Transient Thermal Response Curve**

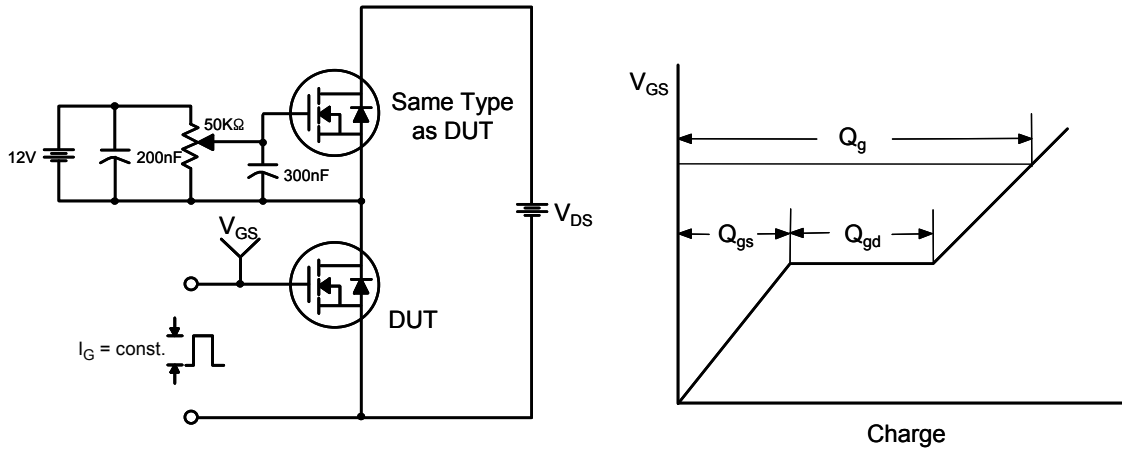


Figure 12. Gate Charge Test Circuit & Waveform

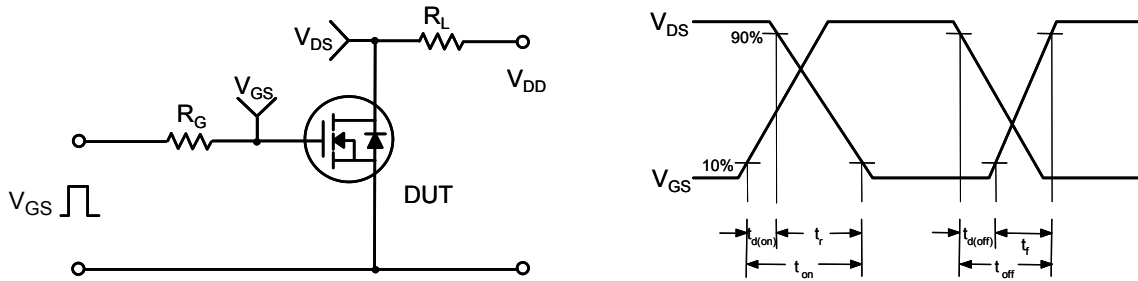


Figure 13. Resistive Switching Test Circuit & Waveforms

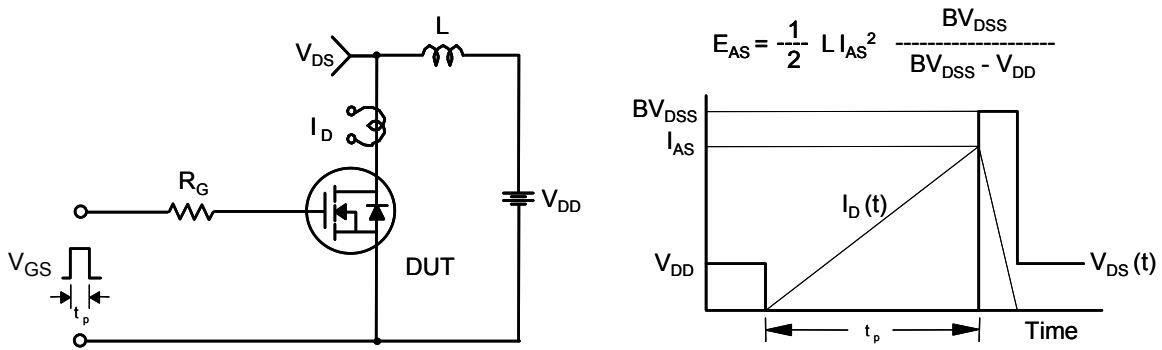


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

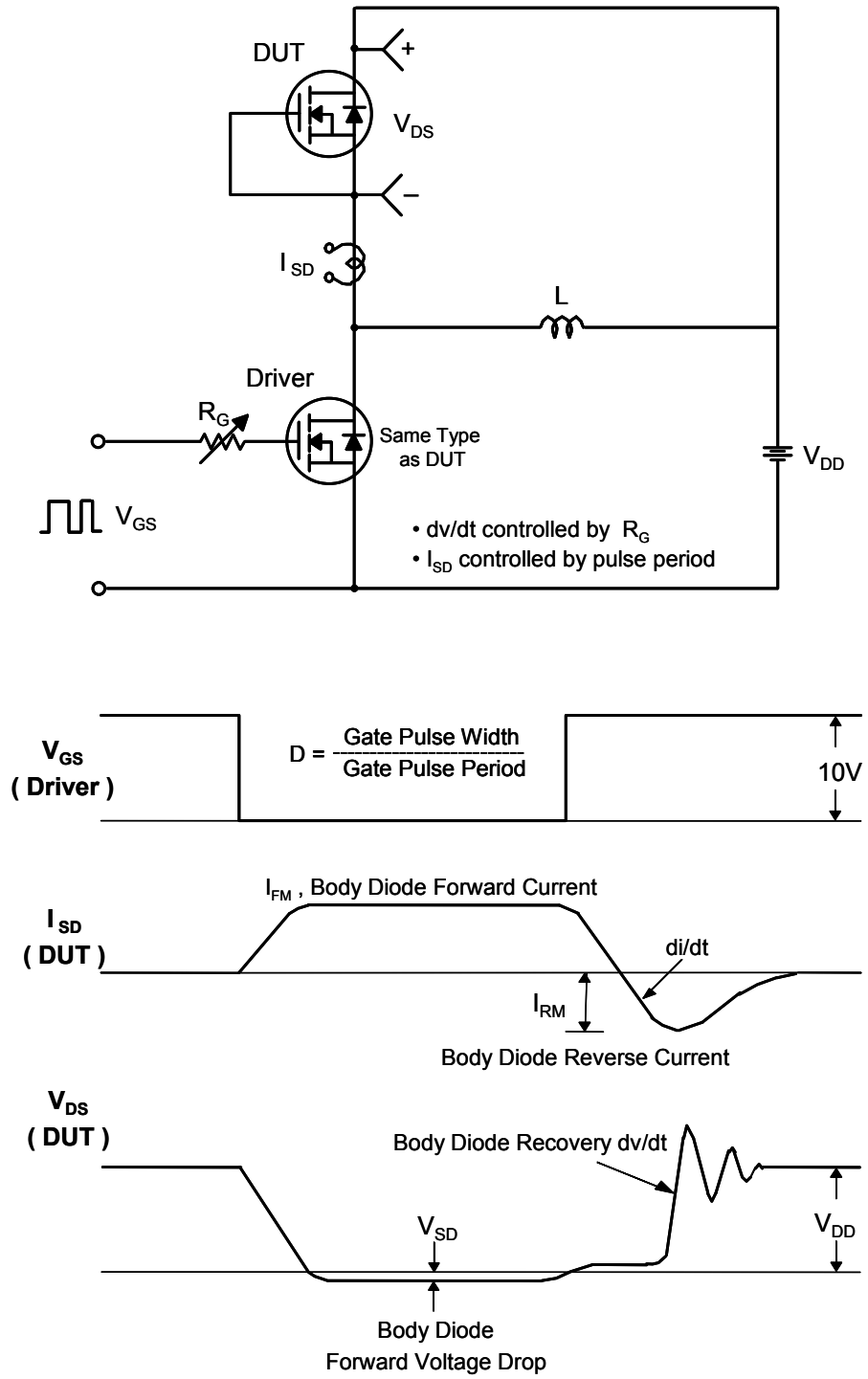
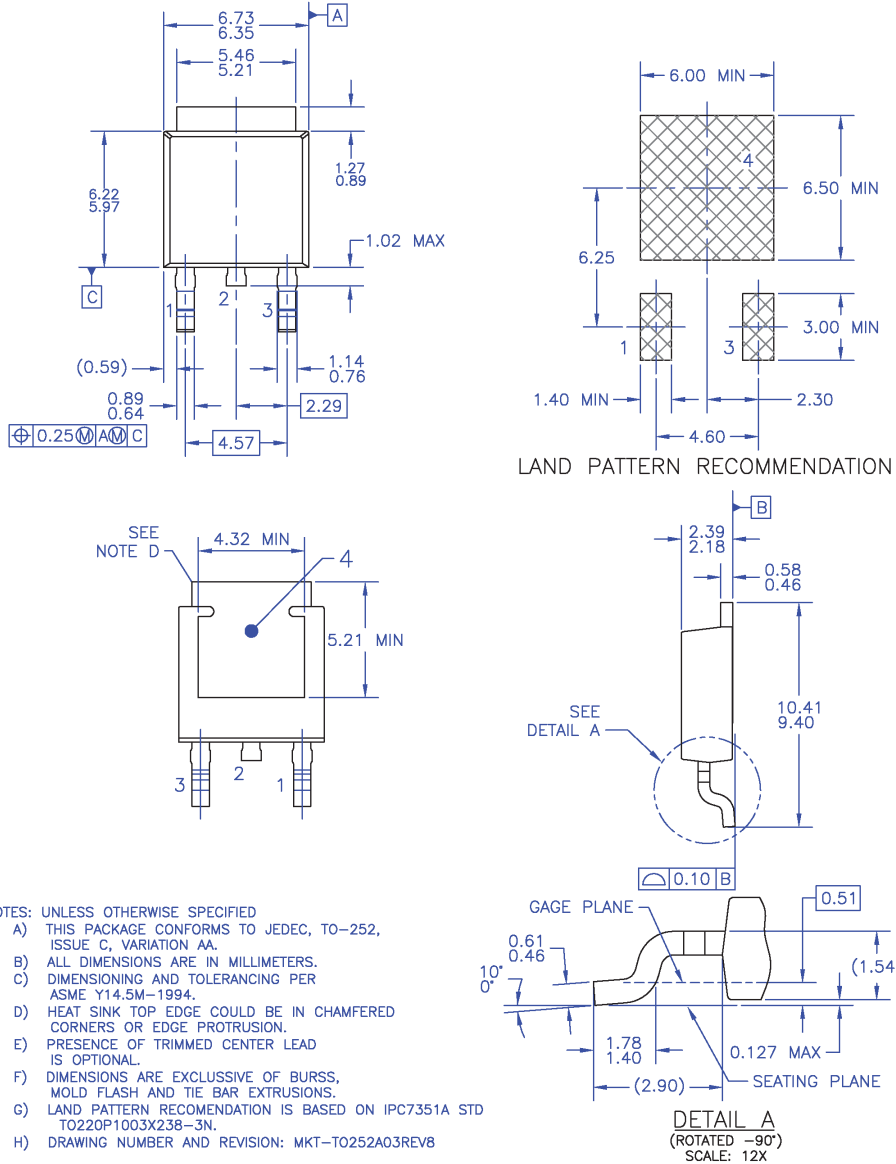


Figure 15. Peak Diode Recovery  $dv/dt$  Test Circuit & Waveforms

**Mechanical Dimensions**



**Figure 16. TO252 (D-PAK), Molded, 3-Lead, Option AA&AB**

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